



Low Voltage Dual SPDT Analog Switch

PI5A23157

#### **Features**

- CMOS Technology for Bus and Analog Applications
- Low propagation delay
- Low typical On-Resistance
- Signal passing bandwidth, 220 MHz
- Wide V<sub>DD</sub> Range: 1.65V to 5.5V
- Rail-to-Rail Signal Range
- High Off Isolation: -65dB @ 10MHz
- Crosstalk Rejection Reduces Signal Distortion: -66dB @ 10MHz
- Break-Before-Make Switching
- Extended Industrial Temperature Range: -40°C to 125°C
- ESD protection : 2kV(HBM)
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/104/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please <u>contact us</u> or your local Diodes representative.

https://www.diodes.com/quality/product-definitions/

- Packaging (Pb-free & Green):
  - 10-pin UQFN (ZUA), 2mm x 1.5mm
  - 10-pin MSOP (U), 3mm x 3mm

### **Applications**

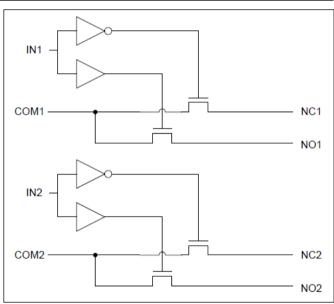
- Sample-and-Hold Circuits
- Battery-Powered Equipment
- Audio and Video Signal Routing
- Communication Circuits

# Description

The DIODES<sup>™</sup> PI5A23157 is a Dual SPDT Analog Switch. The device can be used as an analog switch or as a low-delay bus switch, and has a wide operating power supply voltage, 1.65V to 5.5V

Break-before-make switching prevents both switches being enabled simultaneously. This eliminates signal disruption during switching.

### **Block Diagram**



Notes:

<sup>1.</sup> No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.

<sup>2.</sup> See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free. 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

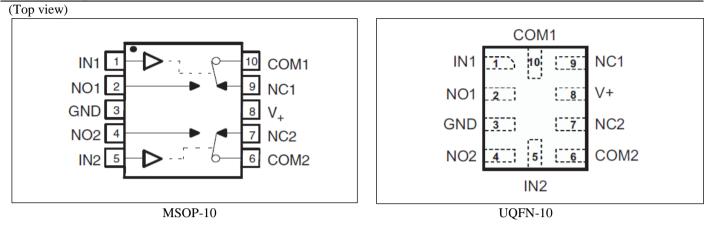
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# **Pin Configuration**



# **Pin Description**

Pin#	Pin Name	Туре	Description
1	IN1	Ι	Select pin for Switch 1
2	NO1	I/O	Normally Open I/O for Switch 1
3	GND	-	Ground
4	NO2	I/O	Normally Open I/O for Switch 2
5	IN2	Ι	Select pin for Switch 2
6	COM2	I/O	Common I/O for Switch 2
7	NC2	I/O	Normally Closed I/O for Switch 2
8	V+	-	Power Supply Pin
9	NC1	I/O	Normally Closed I/O for Switch 1
10	COM1	I/O	Common I/O for Switch 1

### **Function Table**

INx	NC TO COM, COM TO NC	NO TO COM, COM TO NO
L	ON	OFF
Н	OFF	ON





### **Maximum Ratings**

$\label{eq:storage} \begin{array}{c} \mbox{Storage Temperature} & -65^\circ\mbox{C to } +150^\circ\mbox{C} \\ \mbox{Ambient Temperature with Power Applied} & -40^\circ\mbox{C to } +125^\circ\mbox{C} \\ \mbox{Supply Voltage V}_{DD} & -0.5\mbox{Vto } +6\mbox{V} \\ \mbox{Control Input Voltage V}_{INx} & 0\mbox{Vto } +6\mbox{V} \\ \mbox{DC Input Voltage V}_{INPUT} & -0.5\mbox{Vto } +6\mbox{V} \\ \mbox{Continuous Current NO_NC_COM} & -  \pm 50\mbox{mA} \\ \mbox{ESD(HBM)} & -  2\mbox{kV} \\ \mbox{ESD(CDM)} & - \mbox{.lkV} \\ \end{array}$	<b>Note:</b> Stresses greater than those listed under MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability. The input and output negative voltage ratings may be exceeded if the input and output diode current ratings are observed. Control input must be held HIGH or LOW; it must not float.
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### **Recommended Operating Conditions**

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
$V_+$	Operating Voltage	-	1.65	-	5.5	V
V <sub>IN</sub>	Control Input Voltage	-	0	-	V <sub>DD</sub>	V
V <sub>INPUT</sub>	Switch Input Voltage	-	-0.3	-	V <sub>DD</sub>	V
T <sub>A</sub>	Operating Temperature	-	-40	25	125	°C

#### **DC Electrical Characteristics**

+5V Supply (V+ = 4.5V to 5.5V,  $T_A = -40$  °C to 85 °C, unless otherwise noted. Typical values are at 5V and +25 °C.)

Parameter	Symbol	Test Conditions	Temp.	Min.	Typ.	Max.	Units
ANALOG SWITCH							
Analog Signal Range	V <sub>NO</sub> , V <sub>NC</sub> , V <sub>COM</sub>			0	-	V+	V
On-Resistance	R <sub>ON</sub>	$\label{eq:lcom} \begin{split} I_{COM} = -30 mA, \ 0 \leq V_{NO} \ or \ V_{NC} \leq V+, \\ \textit{Test Circuit 1} \end{split}$	-40°C to 85°C -40°C to 125°C	-		10 15	Ω
On-Resistance Match Between Channels	$\Delta R_{\rm ON}$	$I_{COM} = -30$ mA, $V_{NO}$ or $V_{NC} = 3.15$ V, Test Circuit 1	+25°C		0.15		Ω
On-Resistance Flatness	R <sub>ONF</sub>	$I_{COM} = -30 \text{mA}, 0 \le V_{NO} \text{ or } V_{NC} \le V+,$ Test Circuit 1	+25°C		4		Ω
NC/NO Channel-Off	I <sub>OFF (NO)</sub> or	$V_{NO}$ or $V_{NC} = 0$ to V+,	+25°C	-1	0.05	1	μA
Leakage Current	I <sub>OFF (NC)</sub>	$V_{COM} = 0$ to V+	-40°C to 85°C	-1		1	μΑ
NC/NO Channel-ON	I <sub>ON (NO)</sub> or	$V_{NO}$ or $V_{NC} = 0$ to V+,	+25°C	-0.1		0.1	μΑ
Leakage Current	$I_{ON(NC)}$	$V_{COM} = 0$ to V+	-40°C to 85°C	-1		1	μΑ
COM - On Leakage	T	$V_{NO}$ or $V_{NC}$ = open & $V_{COM}$ = 0 to	+25°C	-0.1		0.1	
Current	$I_{COM (ON)}$	V+ -40°C to	-40°C to 85°C	-1		1	μΑ
DIGITAL INPUTS (IN	1, IN2)						
Input Logic High	V		-40°C to 85°C	0.7xV+			
Input Logic High	$V_{IH}$	-	-40°C to 125°C	3.1			V
Input Logic Low	V <sub>IL</sub>	-	-40°C to 85°C			0.3xV+	
IN Input Leakage	т	$V + = 5.5, V_{IN} = 0 \text{ or } 5.5V$	+25°C	-1	0.05	1	A
Current	$I_{IN}$		-40°C to 85°C	-1		1	μΑ
DYNAMIC CHARACT	TERISTICS						
		$V_{NC}$ =GND, $V_{NO}$ = V+ or $V_{NC}$ = V+,	-40°C to 85°C	1.7		11.5	ns
Turn-On Time	t <sub>ON</sub>	$V_{NO}$ =GND, $R_L$ =500 $\Omega$ , $C_L$ =50pF. See Test Circuit Figure 2.	-40°C to 125°C	1.2		12	ns
		$V_{NC}$ =GND, $V_{NO}$ = V+ or $V_{NC}$ = V+,	-40°C to 85°C	0.8		7.5	ns
Turn-Off Time	t <sub>OFF</sub>	$V_{NO}$ =GND, $R_L$ =500 $\Omega$ , $C_L$ =50pF. See <i>Test Circuit Figure 2</i> .	-40°C to 125°C	0.5		8	ns
Break-Before-Make Delay	t <sub>BBM</sub>	$V_{NC}=V_{NO}=V+/2$ , $R_L=50\Omega$ , $C_L=35pF$ See Test Circuit Figure 3.	-40°C to 85°C	0.5			ns
Charge injection	Qc	Vgen=0V; Rgen=0 RL=1Mohm, CL=35pF	+25°C		7		pC





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Parameter	Symbol	Test Conditions	Temp.	Min.	Тур.	Max.	Units
3dB Bandwidth	$f_{\rm 3dB}$	R <sub>L</sub> =50 Ω. See Test Circuit Figure 6.	+25°C	-	220	-	MHz
COM-NC/NO and NC-NO Isolations	O <sub>ISO</sub>	R <sub>L</sub> =50 Ω, f=10MHz See Test Circuit Figure 4.	+25°C	-	-65	-	dB
Channel-to-Channel Crosstalk	X <sub>TALKD</sub>	R <sub>L</sub> =50 Ω, f=10MHz See Test Circuit Figure 5.	+25°C	-	-66	-	dB
Total harmonic distortion	THD	R <sub>L</sub> =600Ω, C <sub>L</sub> =50pF f=600Hz ~ 20KHz.	+25°C		0.01%		
SUPPLY							
Dowor Supply Current	T	V - CND or V - Switch ON or OFF	+25°C	-	-	1	
Power Supply Current	I <sub>CC</sub>	$V_{IN}$ =GND or V+, Switch ON or OFF	-40°C to 85°C	-	-	10	μA

### +3.3V Supply (V+ = 3V to 3.6V, $T_A = -40$ °C to 85 °C, unless otherwise noted. Typical values are at 3.3V and +25 °C.)

Parameter	Symbol	Test Conditions	Temp.	Min.	Тур.	Max.	Units
ANALOG SWITCH							
Analog Signal Range	V <sub>NO</sub> , V <sub>NC</sub> , V <sub>COM</sub>			0	-	V+	V
On-Resistance	R <sub>ON</sub>	$I_{COM} = -24 m A, \ 0 \leq V_{NO} \ \text{or} \ V_{NC} \leq V^+,$	-40°C to 85°C	-		18	Ω
	NON	Test Circuit 1	-40°C to 125°C	-		23	55
On-Resistance Match Between Channels	$\Delta R_{\rm ON}$	$I_{COM} = -24mA$ , $V_{NO}$ or $V_{NC} = 2.1V$ , Test Circuit 1	+25°C		0.2		Ω
On-Resistance Flatness	R <sub>ONF</sub>	$\label{eq:lcom} \begin{split} I_{COM} = -24 m A, \ 0 \leq V_{NO} \ or \ V_{NC} \leq V+, \\ \textit{Test Circuit 1} \end{split}$	+25°C		9		Ω
NC/NO Channel-Off	$I_{OFF(NO)}$ or	$V_{NO}$ or $V_{NC} = 0$ to V+,	+25°C	-1	0.05	1	μΑ
Leakage Current	I <sub>OFF (NC)</sub>	$V_{COM} = 0$ to V+	-40°C to 85°C	-1		1	μΑ
NC/NO Channel-ON	$I_{ON(NO)}$ or	$V_{NO}$ or $V_{NC} = 0$ to V+,	+25°C	-0.1		0.1	μΑ
Leakage Current	I <sub>ON (NC)</sub>	$V_{COM} = 0$ to V+	-40°C to 85°C	-1		1	μл
COM - On Leakage	T	$V_{NO}$ or $V_{NC}$ = open & $V_{COM}$ = 0 to	+25°C	-0.1		0.1	
Current	$I_{COM (ON)}$	V+	-40°C to 85°C	-1		1	μA
DIGITAL INPUTS (IN	1, IN2)						
Input Logic High	V <sub>IH</sub>	-	-40°C to 85°C	0.7xV+			V
Input Logic Low	V <sub>IL</sub>	-	-40°C to 85°C			0.3xV+	v
IN Input Leakage	т	$V + = 3.6, V_{IN} = 0 \text{ or } 3.6V$	+25°C	-1	0.05	1	
Current	$I_{IN}$		-40°C to 85°C	-1		1	μΑ
DYNAMIC CHARACT	TERISTICS						
		$V_{NC}$ =GND, $V_{NO}$ = V+ or $V_{NC}$ = V+,	-40°C to 85°C	2.5		13	ns
Turn-On Time	t <sub>ON</sub>	$V_{NO}$ =GND, $R_L$ =500 $\Omega$ , $C_L$ =50pF. See Test Circuit Figure 2.	-40°C to 125°C	2.0		14	ns
		$V_{NC}$ =GND, $V_{NO}$ = V+ or $V_{NC}$ = V+,	-40°C to 85°C	1.5		8.5	ns
Turn-Off Time	t <sub>OFF</sub>	$V_{NO}$ =GND, $R_L$ =500 $\Omega$ , $C_L$ =50pF. See <i>Test Circuit Figure 2</i> .	-40°C to 125°C	1.0		9	ns
Break-Before-Make Delay	t <sub>BBM</sub>	$V_{NC}=V_{NO}=V+/2$ , $R_L=50\Omega$ , $C_L=35pF$ See Test Circuit Figure 3.	-40°C to 85°C	0.5			ns
Charge injection	Qc	Vgen=0V; Rgen=0 RL=1Mohm, CL=35pF	+25°C		3		pC
3dB Bandwidth	$\mathbf{f}_{3dB}$	R <sub>L</sub> =50Ohm. <i>See Test Circuit Figure 6.</i>	+25°C	-	220	-	MHz
COM-NC/NO and NC-NO Isolations	O <sub>ISO</sub>	R <sub>L</sub> =50Ohm, f=10MHz See Test Circuit Figure 4.	+25°C	-	-65	-	dB
Channel-to-Channel Crosstalk	X <sub>TALKD</sub>	R <sub>L</sub> =50Ohm, f=10MHz See Test Circuit Figure 5.	+25°C	-	-66	-	dB
Total harmonic	THD	R <sub>L</sub> =600 $\Omega$ , C <sub>L</sub> =50pF f=600Hz ~	+25°C		0.015%		





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Parameter	Symbol	Test Conditions	Temp.	Min.	Тур.	Max.	Units
distortion		20KHz.					
SUPPLY							
Dowon Symply Cymont	т	V - CND or V Switch ON or OFF	+25 °C	-	-	1	
Power Supply Current	I <sub>CC</sub>	V <sub>IN</sub> =GND or V+, Switch ON or OFF	-40°C to 85°C	-	-	10	μА

### +2.5V Supply (V+ = 2.3V to 2.7V, $T_A = -40^{\circ}$ C to 85°C, unless otherwise noted. Typical values are at 2.5V and +25°C.)

Parameter	Symbol	Test Conditions	Temp.	Min.	Typ.	Max.	Units
ANALOG SWITCH		· · · ·					
Analog Signal Range	V <sub>NO</sub> , V <sub>NC</sub> , V <sub>COM</sub>			0	-	V+	V
On-Resistance	R <sub>ON</sub>	$I_{COM} = -8mA, 0 \le V_{NO} \text{ or } V_{NC} \le V+,$ Test Circuit 1	-40°C to 85°C -40°C to 125°C	-		45 50	Ω
On-Resistance Match Between Channels	$\Delta R_{ON}$	$I_{COM} = -8mA$ , $V_{NO}$ or $V_{NC} = 1.6V$ , Test Circuit 1	+25°C		0.5		Ω
On-Resistance Flatness	R <sub>ONF</sub>	$I_{COM} = -8mA, 0 \le V_{NO} \text{ or } V_{NC} \le V+,$ Test Circuit 1	+25°C		27		Ω
NC/NO Channel-Off Leakage Current	$I_{OFF (NO)}$ or $I_{OFF (NC)}$	$V_{NO} \text{ or } V_{NC} = 0 \text{ to } V+,$ $V_{COM} = 0 \text{ to } V+$	+25°C -40°C to 85°C	-1 -1	0.05	1	μΑ
NC/NO Channel-ON Leakage Current	I <sub>ON (NO)</sub> or I <sub>ON (NC)</sub>	$V_{NO}$ or $V_{NC} = 0$ to V+, $V_{COM} = 0$ to V+	+25°C -40°C to 85°C	-0.1		0.1	μΑ
COM - On Leakage Current	I <sub>COM (ON)</sub>	$V_{NO}$ or $V_{NC}$ = open & $V_{COM}$ = 0 to $V_{+}$	+25°C -40°C to 85°C	-0.1 -1		0.1	μΑ
DIGITAL INPUTS (IN	1, IN2)			_		-	
Input Logic High	V <sub>IH</sub>	-	-40°C to 85°C	0.7xV+			
Input Logic Low	V <sub>IL</sub>	-	-40°C to 85°C			0.3xV+	V
IN Input Leakage Current	I <sub>IN</sub>	$V_{+} = 2.7, V_{IN} = 0 \text{ or } 2.7V$	+25°C -40°C to 85°C	-1 -1	0.05	1	μΑ
DYNAMIC CHARACT	TERISTICS			-		-	
		$V_{NC}$ =GND, $V_{NO}$ = V+ or $V_{NC}$ = V+,	-40°C to 85°C	3.5		14	ns
Turn-On Time	t <sub>ON</sub>	$V_{NO}$ =GND, $R_L$ =500 $\Omega$ , $C_L$ =50pF. See Test Circuit Figure 2.	-40°C to 125°C	2.5		17	ns
		$V_{NC}$ =GND, $V_{NO}$ = V+ or $V_{NC}$ = V+,	-40°C to 85°C	2		9.5	ns
Turn-Off Time	t <sub>OFF</sub>	$V_{NO}$ =GND, $R_L$ =500 $\Omega$ , $C_L$ =50pF. See Test Circuit Figure 2.	-40°C to 125°C	1.5		10	ns
Break-Before-Make Delay	t <sub>BBM</sub>	$V_{NC}=V_{NO}=V+/2$ , $R_L=50\Omega$ , $C_L=35pF$ See Test Circuit Figure 3.	-40°C to 85°C	0.5			ns
3dB Bandwidth	$f_{3dB} \\$	R <sub>L</sub> =500hm. See Test Circuit Figure 6.	+25°C	-	220	-	MHz
COM-NC/NO and NC-NO Isolations	O <sub>ISO</sub>	R <sub>L</sub> =500hm, f=10MHz See Test Circuit Figure 4.	+25°C	-	-65	-	dB
Channel-to-Channel Crosstalk	X <sub>TALKD</sub>	R <sub>L</sub> =500hm, f=10MHz See Test Circuit Figure 5.	+25°C	-	-66	-	dB
Total harmonic distortion	THD	R <sub>L</sub> =600Ω, C <sub>L</sub> =50pF f=600Hz ~ 20KHz.	+25°C		0.025%		
SUPPLY				r	[		
Power Supply Current	I+	V <sub>IN</sub> =GND or V+, Switch ON or OFF	+25°C -40°C to 85°C	-	-	1 10	μΑ



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Parameter	Symbol	Test Conditions	Temp.	Min.	Typ.	Max.	Units
ANALOG SWITCH		·1		-			
Analog Signal Range	V <sub>NO</sub> , V <sub>NC</sub> , V <sub>COM</sub>			0	-	$\mathbf{V}$ +	V
On-Resistance	R <sub>ON</sub>	$I_{COM} = -4mA, 0 \le V_{NO} \text{ or } V_{NC} \le V+,$ Test Circuit 1	-40°C to 85°C -40°C to 125°C	-		140 180	Ω
On-Resistance Match Between Channels	$\Delta R_{\rm ON}$	$I_{COM} = -4mA$ , $V_{NO}$ or $V_{NC} = 1.15V$ , Test Circuit 1	+25°C		1		Ω
On-Resistance Flatness	R <sub>ONF</sub>	$\label{eq:loss_com} \begin{split} I_{COM} &= -4mA, \ 0 \leq V_{NO} \ \text{or} \ V_{NC} \leq V+, \\ \textit{Test Circuit 1} \end{split}$	+25°C		110		Ω
NC/NO Channel-Off Leakage Current	$I_{OFF (NO)}$ or $I_{OFF (NC)}$	$V_{NO}$ or $V_{NC} = 0$ to V+, $V_{COM} = 0$ to V+	+25°C -40°C to 85°C	-1 -1	0.05	1	μΑ
NC/NO Channel-ON Leakage Current	$I_{ON (NO)}$ or $I_{ON (NC)}$	$V_{NO}$ or $V_{NC} = 0$ to V+, $V_{COM} = 0$ to V+	+25°C -40°C to 85°C	-0.1		0.1	μΑ
COM - On Leakage Current		$V_{NO}$ or $V_{NC}$ = open & $V_{COM}$ = 0 to V+	+25°C -40°C to 85°C	-1 -0.1 -1		0.1 1	μΑ
DIGITAL INPUTS (IN	1, IN2)						
Input Logic High	V <sub>IH</sub>	-	-40°C to 85°C	0.75xV +			v
Input Logic Low	V <sub>IL</sub>	-	-40°C to 85°C			0.25xV +	v
IN Input Leakage Current	$I_{IN}$	$V_{+} = 1.95, V_{IN} = 0 \text{ or } 1.95V$	+25°C -40°C to 85°C	-1 -1	0.05	1	μΑ
DYNAMIC CHARACT	FERISTICS		10 0 10 05 0	-		1	
	21051105	$V_{NC}$ =GND, $V_{NO}$ = V+ or $V_{NC}$ = V+,	-40°C to 85°C	7		24	ns
Turn-On Time	t <sub>ON</sub>	$V_{NO}$ =GND, $R_L$ =500 $\Omega$ , $C_L$ =50pF. See Test Circuit Figure 2.	-40°C to 125°C	5.5		27	ns
		$V_{NC}$ =GND, $V_{NO}$ = V+ or $V_{NC}$ = V+,	-40°C to 85°C	3		13	ns
Turn-Off Time	t <sub>OFF</sub>	$V_{NO}$ =GND, $R_L$ =500 $\Omega$ , $C_L$ =50pF. See <i>Test Circuit Figure 2.</i>	-40°C to 125°C	2		16	ns
Break-Before-Make Delay	t <sub>BBM</sub>	$V_{NC}=V_{NO}=V+/2$ , $R_L=50\Omega$ , $C_L=35pF$ See Test Circuit Figure 3.	-40°C to 85°C	0.5			ns
3dB Bandwidth	$f_{3dB} \\$	R <sub>L</sub> =50Ohm. <i>See Test Circuit Figure 6.</i>	+25°C	-	220	-	MHz
COM-NC/NO and NC-NO Isolations	O <sub>ISO</sub>	R <sub>L</sub> =50Ohm, f=10MHz See Test Circuit Figure 4.	+25°C	-	-65	-	dB
Channel-to-Channel Crosstalk	X <sub>TALKD</sub>	R <sub>L</sub> =500hm, f=10MHz See Test Circuit Figure 5.	+25°C	-	-66	-	dB
Total harmonic distortion	THD	$R_L$ =600Ω, $C_L$ =50pF f=600Hz ~ 20KHz.	+25°C		0.015%		
SUPPLY		ı					
Power Supply Current	I+	V <sub>IN</sub> =GND or V+, Switch ON or OFF	+25°C	-	-	1	μA
Tower Suppry Current			-40°C to 85°C	-	-	10	•

+1.8V Supply (V+ = 1.65V to 1.95V,  $T_A = -40^{\circ}$ C to 85°C, unless otherwise noted. Typical values are at 1.8V and +25°C.)





#### Capacitance

Capacitance						
Parameter	Symbol	Test Conditions		Тур.	Max.	Units
NC/NO Off	C	$V_{NC}$ or $V_{NO} = V_{DD}$ or GND, Switch OFF		5.5		
Capacitance	C <sub>NC/NO (OFF)</sub>	f = 1MHz, See Test Circuit Figure 7.		5.5	-	
NC/NO On	C	$V_{NC}$ or $V_{NO} = V_{DD}$ or GND, Switch ON		175		
Capacitance	C <sub>NC/NO (ON)</sub>	f = 1MHz, See Test Circuit Figure 8.	-	17.5	-	πE
COM On	C	$V_{NC}$ or $V_{NO} = V_{DD}$ or GND, Switch ON		17.5		pF
Capacitance	C <sub>COM (ON)</sub>	f = 1MHz, See Test Circuit Figure 8.	-	17.5	-	
Digital Input	C	f = 1MHz		2.8		
Capacitance	C <sub>IN</sub>	I = IWHZ	-	2.8	-	





CL

50 pF

50 pF

50%

VNC

GND

V+

GND

V+

90%

50%

VNO

V+

GND

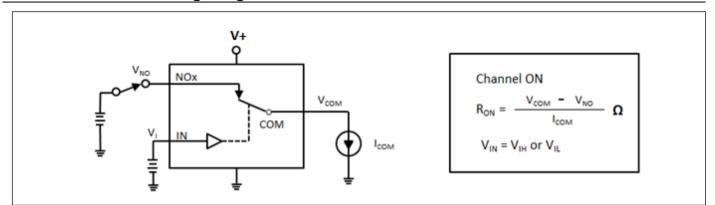
V+

GND

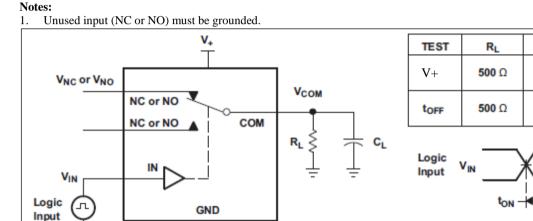
tOFF

90%

## **Test Circuits and Timing Diagrams**



#### Figure 1. On Resistance



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Figure 2. Switching Times

Switch

Output

V<sub>COM</sub>

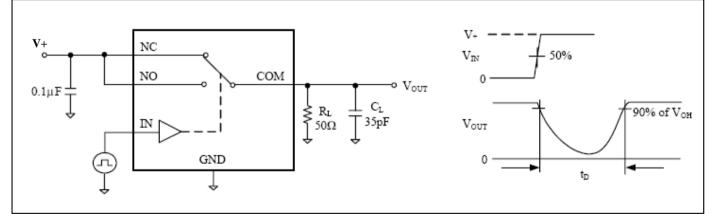
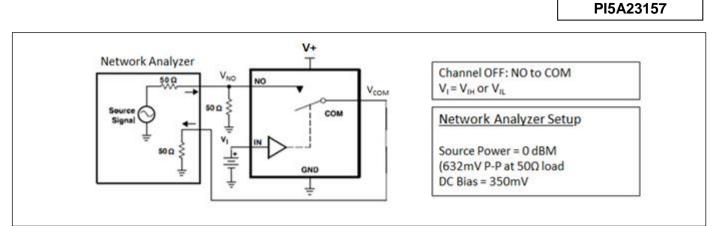


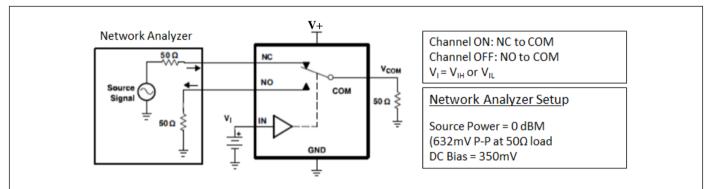
Figure 3. Break Before Make Interval Timing







### Figure 4. OFF Isolation (O<sub>ISO</sub>)



### Figure 5. Channel-to-Channel Crosstalk

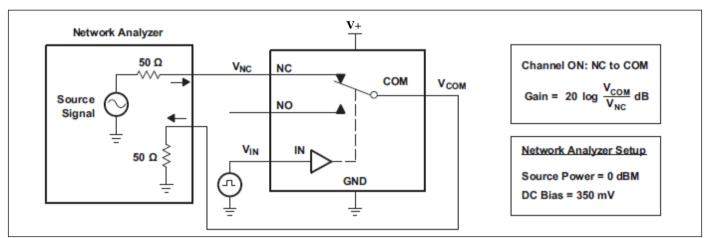


Figure 6. Bandwidth



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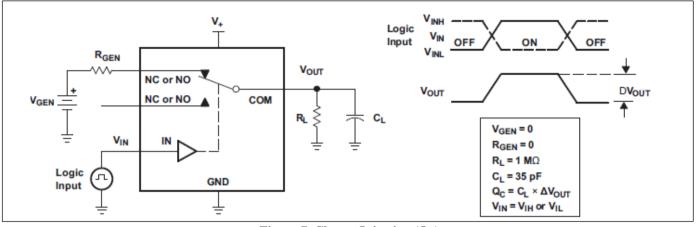


Figure 7. Charge Injection  $(Q_C)$ 

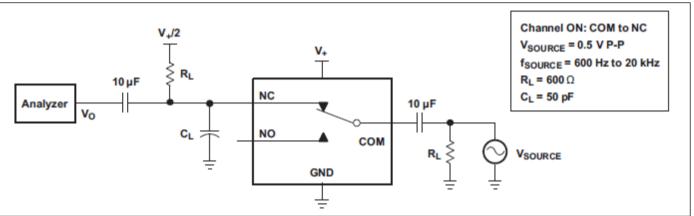


Figure 8. Total Harmonic Distortion (THD)

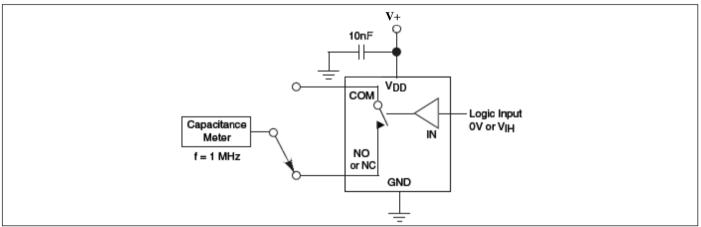
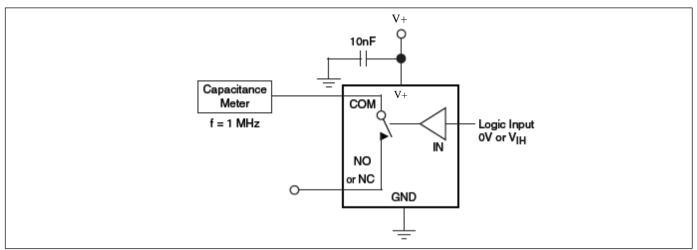


Figure 9. Channel Off Capacitance



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### Figure 10. Channel On Capacitance

## **Part Marking**

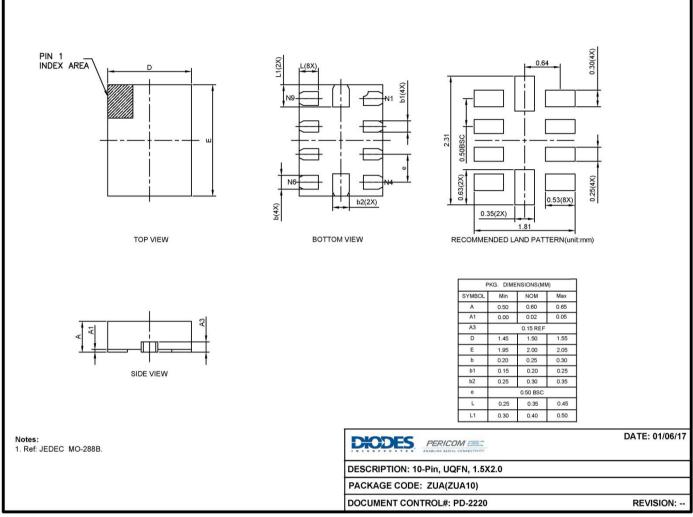
ZUA Package	U Package
• FE YW	PI5A23 157UE
	YWXX
FE: PI5A23157ZUAE	Y: Date Code (Year)
Y: Date Code (Year)	W: Date Code (Workweek)
W: Date Code (Workweek)	1st X: Assembly Site Code 2nd X: Fab Site Code
Line above 1st chatacter denotes Lead-free and pin 1 indicator	Bar above 2nd "X" means Cu wire





# **Packaging Mechanical**



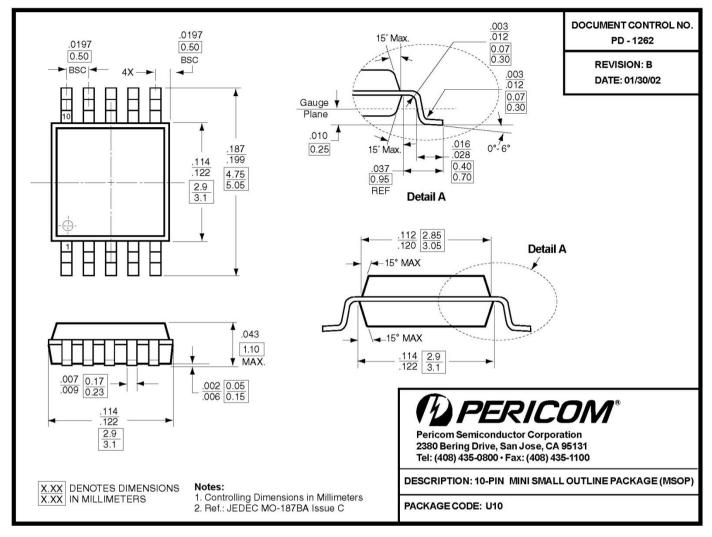


17-0002





### 10-MSOP (U)



#### For latest package info.

please check: http://www.diodes.com/design/support/packaging/pericom-packaging/packaging-mechanicals-and-thermal-characteristics/

### **Ordering Information**

Part Number	Packaging Code	Package Description
PI5A23157ZUAEX	ZUA	10-Pin, 1.5mm x 2.0mm (UQFN)
PI5A23157UEX	U	10-Pin, Mini Small Outline Package (MSOP)

#### Notes:

No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.

2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. E = Pb-free and Green

5. X suffix = Tape/Reel





PI5A23157

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